62

4.9...60

1

-30 ... +85

 $V_{\rm bbin(AZ)}$

 $V_{\rm bb(on)}$

 $R_{\rm ON}$

Ta

V

V

Ω

°C

Smart High-Side Power Switch for Industrial Applications One channel: $1 \times 1 \Omega$

Features

- Current controlled input
- Short circuit protection
- Current limitation
- Overload protection
- Overvoltage protection (including load dump)
- Switching inductive loads
- Clamp of negative voltage at output with inductive loads
- Thermal shutdown with restart
- ESD Protection
- Loss of GND and loss of $V_{\mbox{\scriptsize bb}}$ protection
- Very low standby current
- Reverse battery protection
- Improved electromagnetic compatibility (EMC)

Application

- All types of resistive, inductive and capacitive loads in industrial applications
- Current controlled power switch for 12V, 24V and 42V DC industrial applications

Product Summary

Operating voltage

On-state resistance

Overvoltage protection

Operating Temperature

- Driver for electromagnetic relays
- Signal amplifier

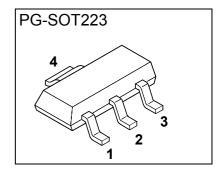
General Description

• N channel vertical power MOSFET with charge pump and current controlled input, monolithically integrated in Smart SIPMOS® technology.

Page 1

• Providing embedded protection functions.

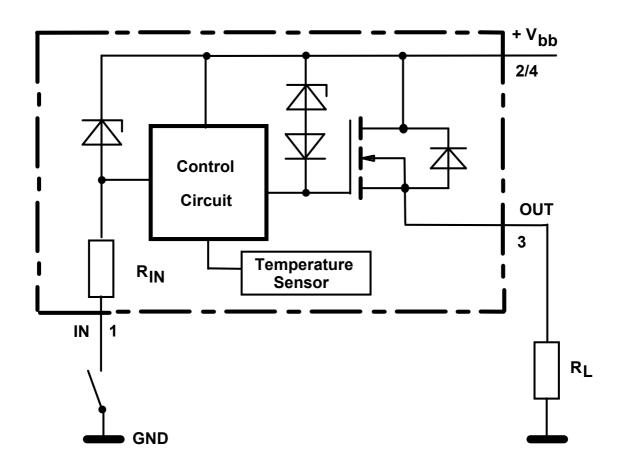
Туре	Ordering code	Package
ITS 4140N	SP000240073	PG-SOT223







Block Diagram



Pin	Symbol	Function
1	IN	Input, activates the power switch in case of connection to GND
2	Vbb	Positive power supply voltage
3	OUT	Output to the load
4	Vbb	Positive power supply voltage



Maximum Ratings

Parameter at $T_j = 25^{\circ}$ C unless otherwise specified	Symbol	Values	Unit
Supply voltage	V _{bb}	60	V
Load current (Short – circuit current, see page 5)	١Ĺ	self limited	A
Maximum current through the input pin (DC)	/ _{IN}	±15	mA
Junction temperature Operating temperature range Storage temperature range	T _j T _a T _{stg}	+150 -30 +85 -40+105	°C
Power dissipation ¹⁾ $T_a = 25 \text{ °C}$	P _{tot}	1.7	W
Inductive load switch-off energy dissipation ²⁾ Single pulse $T_j = 150^{\circ}$ C, $I_{L} = 0.15$ A	EAS	1	J
Load dump protection ³⁾ $V_{\text{LoadDump}}^{4} = V_{\text{A}} + V_{\text{S}}$ $R_{\text{L}}=2\Omega$, $t_{\text{d}} = 400$ ms, $V_{\text{IN}} = $ low or high $I_{\text{L}} = 150$ mA, $V_{\text{bb}} = 13.5$ V $V_{\text{bb}} = 27$ V	VLoadDump	93.5 127	V
Electrostatic discharge voltage (Human Body Model) According to ANSI EOS/ESD – S5.1 – 1993 ESD STM5.1 – 1998 Input pin all other pins	VESD	±1 ±5	kV

¹ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

² Not subject to production test, specified by design

³ More details see EMC-Characteristics on page 7

 4 V_{LoadDump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839.



Electrical Characteristics					
Parameter	Symbol		Values	5	Unit
at T_{i} = -40150 °C, V_{bb} = 942 V unless otherwise specified		min.	typ.	max.	
Thermal Characteristics					
Thermal resistance @ min. footprint	R _{th(JA)}	-	86	125	K/W
Thermal resistance @ 6 cm ² cooling area ¹⁾	R _{th(JA)}	-	60	72	
Thermal resistance, junction - soldering point	R _{thJS}	-	-	17	K/W
Load Switching Capabilities and Characteristics					
On-state resistance	R _{ON}				Ω
Pin1 connected to GND					
<i>T</i> _j = 25 °C, <i>I</i> _L = 150 mA, <i>V</i> _{bb} = 952 V		-	1	1.5	
<i>T</i> _j = 150 °C		-	1.5	3	
$T_{\rm j}$ = 25 °C, $I_{\rm L}$ = 50 mA, $V_{\rm bb}$ = 6 V		-	2	5	
Nominal load current ²⁾	I _{L(nom)}	0.2	-	-	A
Device on PCB ¹⁾					
T _a = 85 °C,T _j ≤ 150 °C					
Turn-on time ³⁾ $V_{\rm IN} = V_{\rm bb}$ to 0V to 90% $V_{\rm OUT}$	t _{on}				μs
$R_{\rm L}$ = 270 Ω		-	-	1254)	
$R_{\rm L}$ = 270 Ω , $V_{\rm bb}$ = 13.5 V, $T_{\rm j}$ = 25 °C		-	45	100	
Turn-off time ³⁾ $V_{\rm IN}$ = 0V to $V_{\rm bb}$ to 10% $V_{\rm OUT}$	t _{off}				
$R_{\rm L}$ = 270 Ω		-	-	1754)	
$R_{\rm L}$ = 270 Ω , $V_{\rm bb}$ = 13.5 V, $T_{\rm j}$ = 25 °C		-	40	140	
Slew rate on ³⁾ $V_{\rm IN} = V_{\rm bb}$ to 0V 10 to 30% $V_{\rm OUT}$	dV/dt _{on}				V/µs
$R_{\rm L}$ = 270 Ω		-	-	64)	
$R_{\rm L}$ = 270 Ω , $T_{\rm j}$ = 25 °C, $V_{\rm bb}$ = 13.5 V		-	1.3	4	
Slew rate off ³) $V_{\rm IN} = 0V$ to $V_{\rm bb}$ 70 to 40% $V_{\rm OUT}$	-dV/dt _{off}				
$R_{\rm L}$ = 270 Ω		-	-	84)	
$R_{\rm L}$ = 270 Ω , $T_{\rm j}$ = 25 °C, $V_{\rm bb}$ = 13.5 V		-	1.7	4	

¹Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70 μ m thick) copper area for V_{bb} connection. PCB is vertical without blown air.

 2 Nominal load current is limited by the current limitation (see page 5)

³Timing values only with high input slewrates, otherwise slower.

⁴not subject to production test, specified by design



Electrical Characteristics					
Parameter	Symbol	Values			Unit
at T_j = -40150 °C, V_{bb} = 942 V unless otherwise specified		min.	typ.	max.	
Operating Parameters		•			
Operating voltage	V _{bb(on)}	4.9	-	60	V
Standby current	l _{bb(off)}	-	2	10	μA
Pin1 = open					
Protection Functions ¹					
Initial peak short circuit current limit	I _{L(SCp)}				A
(see page 14)					
7 _j = -40 °C, V _{bb} = 13.5 V, t _m = 100 μs		-	-	1.2	
<i>T</i> _j = 25 °C		-	0.9	-	
<i>T</i> _j = 150 °C		0.2	-	-	
Repetitive short circuit current limit	I _{L(SCr)}	-	0.7	-	
$T_j = T_{jt}$					
Output clamp (inductive load switch off)	V _{ON(CL)}	60	-	-	V
at V _{OUT} = V _{bb} - V _{ON(CL)} ,					
$l_{bb} = 4 \text{ mA}$					
Overvoltage protection	V _{bbin(AZ)}	62	68	-	
/ _{bb} = 1 mA					
Thermal overload trip temperature	T _{jt}	150	-	-	°C
Thermal hysteresis	ΔT_{jt}	-	10	-	К

¹Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.



 $I_{\rm F}$ = 0.2 A, $I_{\rm IN} \le 0.05$ mA

ITS 4140N

Electrical Characteristics					
Parameter	Symbol		Values	•	Unit
_at T_j = -40150 °C, V_{bb} = 942 V unless otherwise specified		min.	typ.	max.	
Input					
Off state input current	I _{IN(off)}				mA
$V_{OUT} \le 0.1 \text{ V}$					
<i>T</i> _j = 25 °C, <i>R</i> _L = 270 Ω		-	-	0.05	
<i>T</i> _j = 150 °C		-	-	0.04	
On state input current (Pin1 grounded) ¹⁾	I _{IN(on)}	-	0.3	1	
Input resistance	RI	0.5	1	2.5	kΩ
Reverse Battery					
Continuous reverse drain current	I _S	-	-	0.2	А
<i>T</i> _C = 25 °C					
Drain-source diode voltage ($V_{OUT} > V_{bb}$)	-V _{ON}	-	600	-	mV

¹Driver circuit must be able to drive currents > 1mA.



EMC-Characteristics

All EMC-Characteristics are based on limited number of sampels and no part of production test.

Test Conditions:

If not other specified the test circuitry is the minimal functional configuration without any external components for protection or filtering.

Supply voltage:	V _{bb} = 13.5V	Temperature:	<i>T</i> _a = 23 ±5°C ;	
Load:	$R_{\rm L}$ = 220 Ω			
Operation mode:	PWM DC On/Off	Frequency:	100Hz / Duty Cycle:	50%
DUT-Specific.:	-			

Fast electrical transients

Acc. ISO 7637

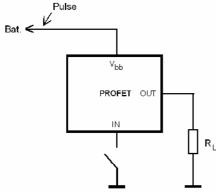
Test Pulse	Test Level	Test Results		Pulse Cycle Time and
		On	Off	Generator Impedance
1	-200 V	С	С	500ms ; 10Ω
2	+200 V	С	C	500ms ; 10Ω
3a	-200 V	С	С	100ms ; 50 Ω
3b	+ 200 V	С	С	100ms ; 50Ω
41)	-7 V	С	С	0,01Ω
5	175 V	E (150V)	E (150V)	400ms ; 2Ω

The test pulses are applied at Vbb

Definition of functional status

Class	Content
С	All functions of the device are performed as designed after exposure to disturbance.
E	One or more function of a device does not perform as designed after exposure
	and can not be returned to proper operation without repairing or replacing the
	device. The value after the character shows the limit.

Test circuit:



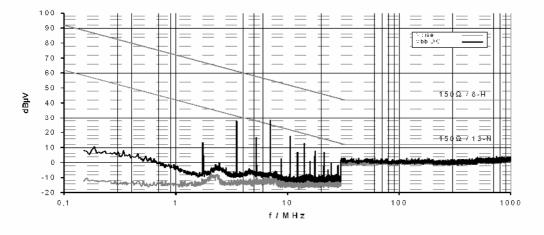
¹Supply voltage V_{bb} = 12 V instead of 13.5 V.



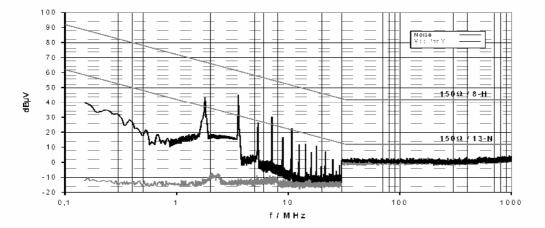
Conducted Emission

Acc. IEC 61967-4 (1 Ω / 150 Ω method)

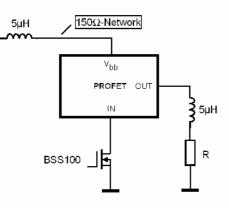
Typ. V_{bb} -Pin Emission at DC-On with 150 Ω -matching network







Test circuit:



For defined decoupling and high reproducibility a defined choke (5 μ H at 1 MHz) is inserted between supply and V_{bb} -pin.

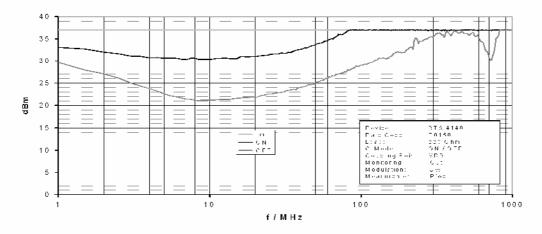


Conducted Susceptibility

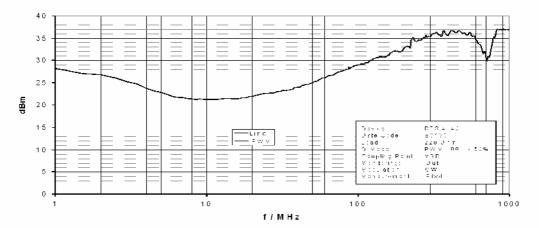
Acc. 47A/658/CD IEC 62132-4 (Direct Power Injection)

Direct Power Injection:	Forward Power CW
Failure criteria:	Amplitude and frequency deviation max. 10% at Out

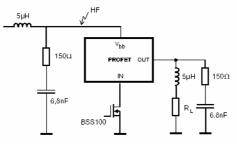
Typ. Vbb-Pin Susceptibility at DC-On/Off







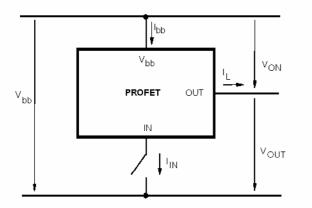
Test circuit:



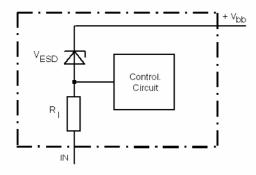
For defined decoupling and high reproducibility the same choke and the same 150Ω -matching network as for the emission measurement is used.



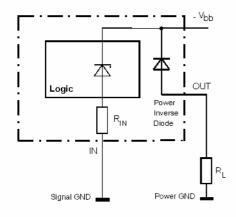
Terms



Input circuit (ESD protection)

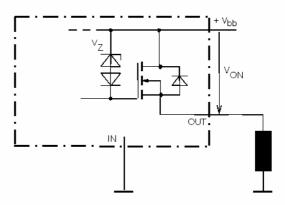


Reverse battery protection



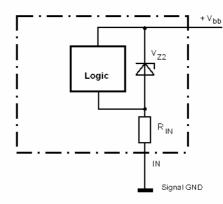
 R_{\parallel} =1k Ω typ., Temperature protection is not active during inverse current.

Inductive and overvoltage output clamp



V_{ON} clamped to 60 V min.

Overvoltage protection of logic part

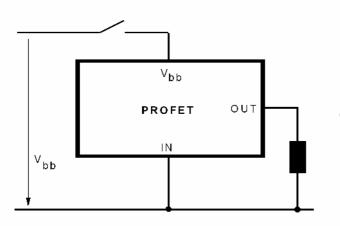


 $V_{bb,AZ} = V_{Z2} + I_{bb} * R_{IN} = 62V \text{ min.}$

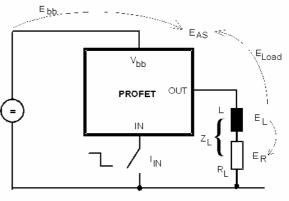


V_{bb} disconnect with charged inductive load

infineon



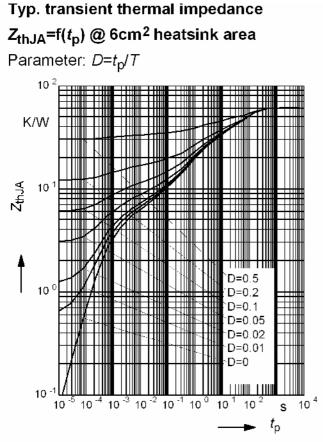
Inductive Load switch-off energy dissipation



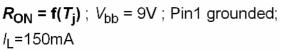
Energy stored in load inductance: $E_L = \frac{1}{2} * L * I_L^2$ While demagnetizing load inductance, the enérgy dissipated in PROFET is $E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} * I_L(t) dt$, with an approximate solution for $R_L > 0\Omega$:

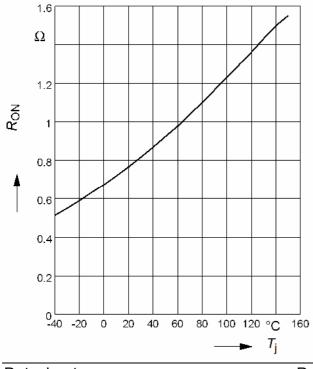
$$E_{AS} = \frac{L}{R_L} \cdot \left(V_{bb} + \left| V_{OUT(CL)} \right| \right) \cdot \left[\frac{-\left| V_{OUT(CL)} \right|}{R_L} \cdot \ln \left(1 + \frac{R_L \cdot I_L}{\left| V_{OUT(CL)} \right|} \right) + I_L \right]$$



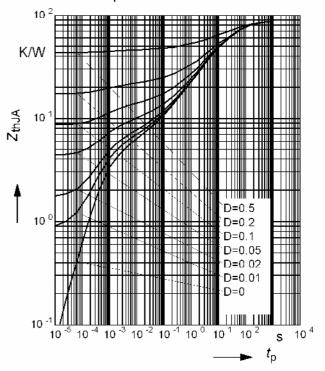


Typ. on-state resistance



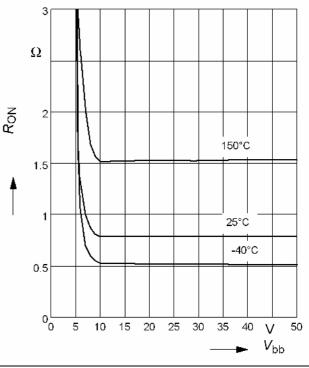


Typ. transient thermal impedance $Z_{thJA}=f(t_p) @ min. footprint$ Parameter: $D=t_p/T$



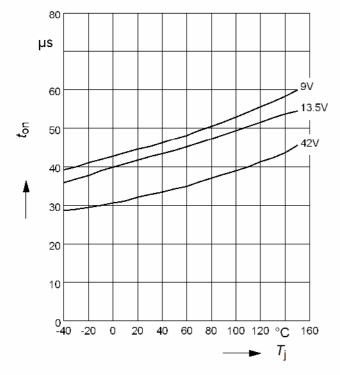
Typ. on-state resistance $R_{\text{even}} = f(V_{\text{even}})$: $L = 150 \text{ mA}^{-1}$ Bin1 group

 R_{ON} = f(V_{bb}); I_{L} = 150mA ; Pin1 grounded

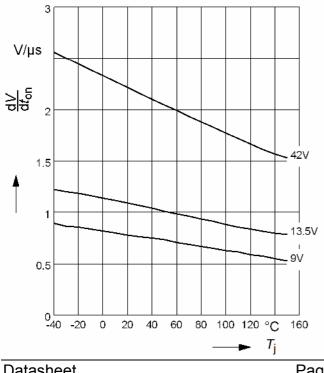




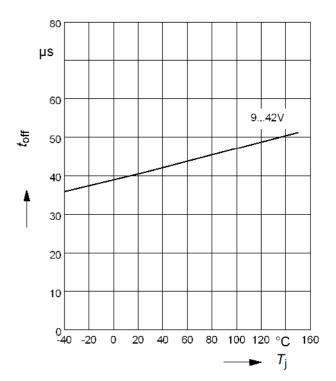
Typ. turn on time $t_{on} = f(T_i); R_L = 270\Omega$



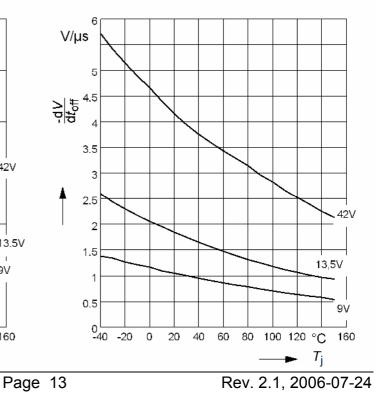
Typ. slew rate on $dV/dt_{on} = f(T_j)$; $R_L = 270 \Omega$



Typ. turn off time $t_{off} = f(T_i); R_L = 270\Omega$

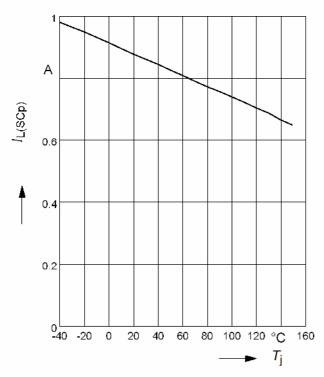


Typ. slew rate off $dV/dt_{off} = f(T_j); R_L = 270 \ \Omega$

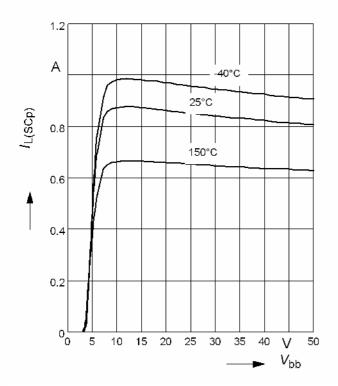




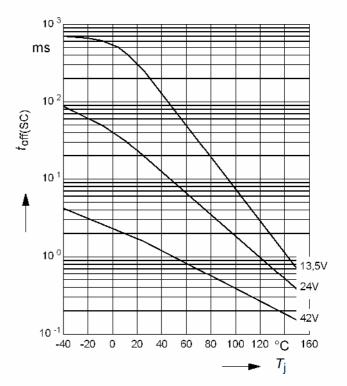
Typ. initial peak short circuit current limit $I_{L(SCp)} = f(T_j)$; $V_{bb} = 13.5$ V; $t_m = 100 \ \mu s$



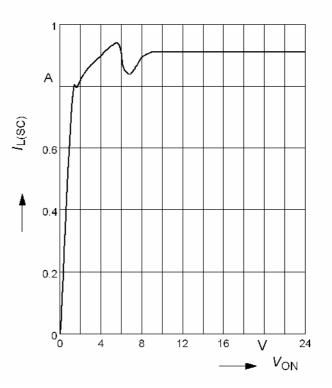
Typ. initial peak short circuit current limit $I_{L(SCp)} = f(V_{bb}); t_m = 100 \ \mu s$



Typ. initial short circuit shutdown time $t_{off(SC)} = f(T_{j,start})$

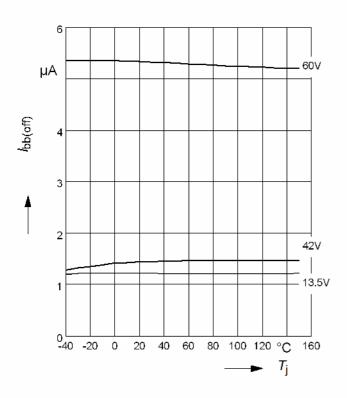


Typ. current limitation characteristic: $I_{L(SC)} = f(V_{ON}), V_{bb} = 13,5V$



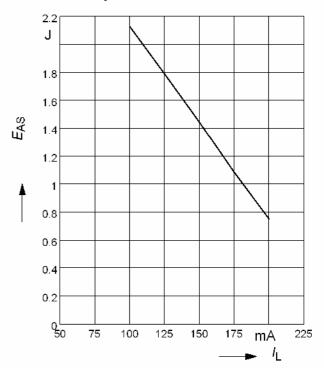


Typ. standby current *I*_{bb(off)} = f(*T*_j) ; Pin1 open



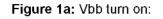
Maximum allowable inductive switch-off energy, single pulse

E_{AS} = f(I_L); T_{jstart} = 150°C





Timing diagrams



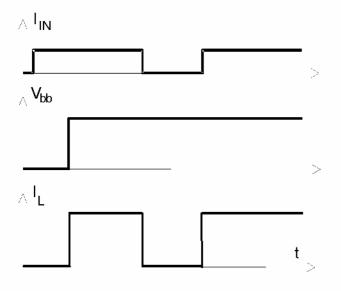


Figure 2b: Switching a lamp

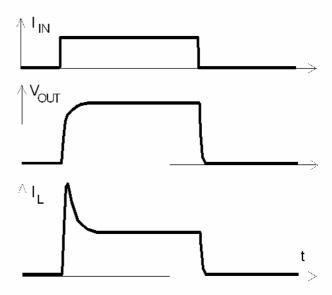


Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition

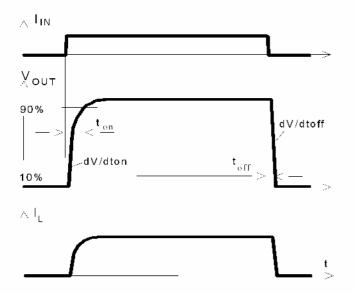


Figure 2c: Switching an inductive load

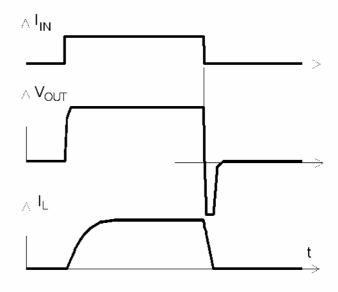
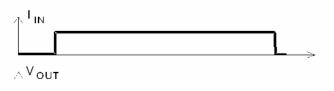
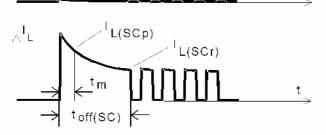




Figure 3a: Turn on into short circuit, shut down by overtemperature, restart by cooling



Output short to GND



Heating up of the chip may require several milliseconds, depending on external conditions.

Figure 4: Overtemperature: Reset if T_i < T_{it}

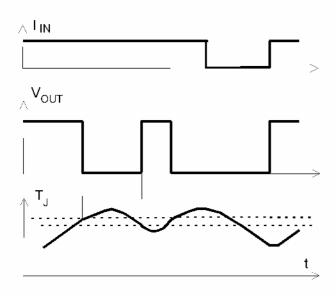
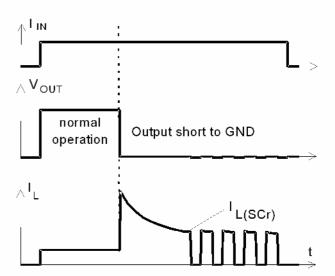


Figure 3b: Short circuit in on-state shut down by overtemperature, restart by cooling

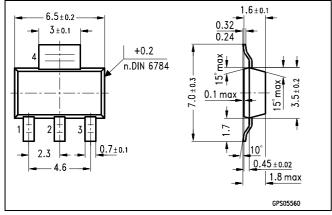




Package and ordering code:

Туре	Ordering code	Package
ITS 4140N	SP000240073	PG-SOT223

all dimensions in mm.



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